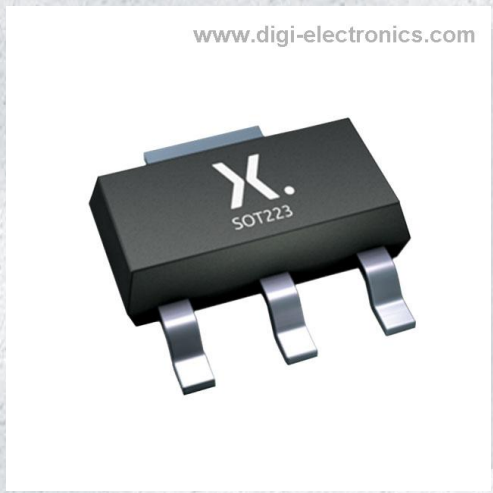
PZT2907A,115 Datasheet



DiGi Electronics Part Number	PZT2907A,115-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PZT2907A,115
Description	TRANS PNP 60V 0.6A SOT223
Detailed Description	Bipolar (BJT) Transistor PNP 60 V 600 mA 200MHz 1 .15 W Surface Mount SOT-223

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

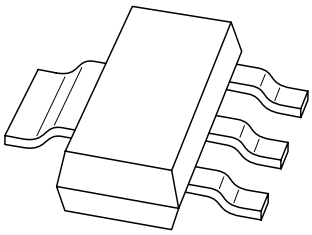
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PZT2907A,115	Nexperia USA Inc.
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	600 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
60 V	1.6V @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10nA (ICBO)	100 @ 150mA, 10V
Power - Max:	Frequency - Transition:
1.15 W	200MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223
Base Product Number:	
PZT2907	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0075	

DATA SHEET



PZT2907A
PNP switching transistor

Product data sheet
Supersedes data of 1997 Jun 02

1999 Apr 14

PNP switching transistor PZT2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a SOT223 plastic package.
NPN complement: PZT2222A.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter

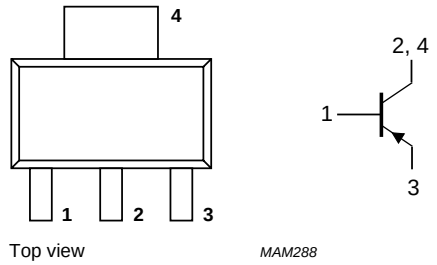


Fig.1 Simplified outline (SOT223) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	−60	V
V_{CEO}	collector-emitter voltage	open base	–	−60	V
V_{EBO}	emitter-base voltage	open collector	–	−5	V
I_C	collector current (DC)		–	−600	mA
I_{CM}	peak collector current		–	−800	mA
I_{BM}	peak base current		–	−200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	1.15	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	106	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point		25	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook".*

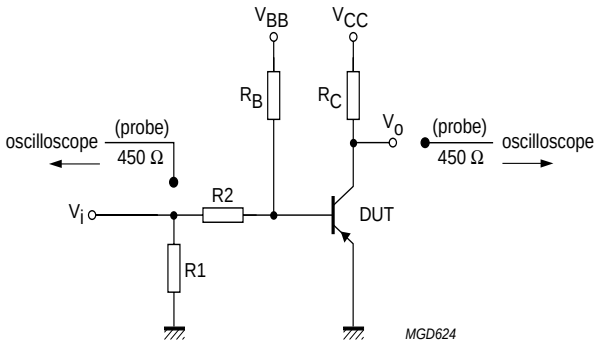
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –50 V	–	–10	nA
		I_E = 0; V_{CB} = –50 V; T_{amb} = 150 °C	–	–10	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –5 V	–	–50	nA
h_{FE}	DC current gain	I_C = –0.1 mA; V_{CE} = –10 V	75	–	
		I_C = –1 mA; V_{CE} = –10 V	100	–	
		I_C = –10 mA; V_{CE} = –10 V	100	–	
		I_C = –150 mA; V_{CE} = –10 V; note 1	100	300	
		I_C = –500 mA; V_{CE} = –10 V; note 1	50	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA; note 1	–	–400	mV
		I_C = –500 mA; I_B = –50 mA; note 1	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA; note 1	–	–1.3	V
		I_C = –500 mA; I_B = –50 mA; note 1	–	–2.6	V
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = –10 V; f = 1 MHz	–	8	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = –2 V; f = 1 MHz	–	30	pF
f_T	transition frequency	I_C = –50 mA; V_{CE} = –20 V; f = 100 MHz; note 1	200	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	I_{Con} = –150 mA; I_{Bon} = –15 mA; I_{Boff} = 15 mA	–	40	ns
t_d	delay time		–	12	ns
t_r	rise time		–	30	ns
t_{off}	turn-off time		–	365	ns
t_s	storage time		–	300	ns
t_f	fall time		–	65	ns

Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

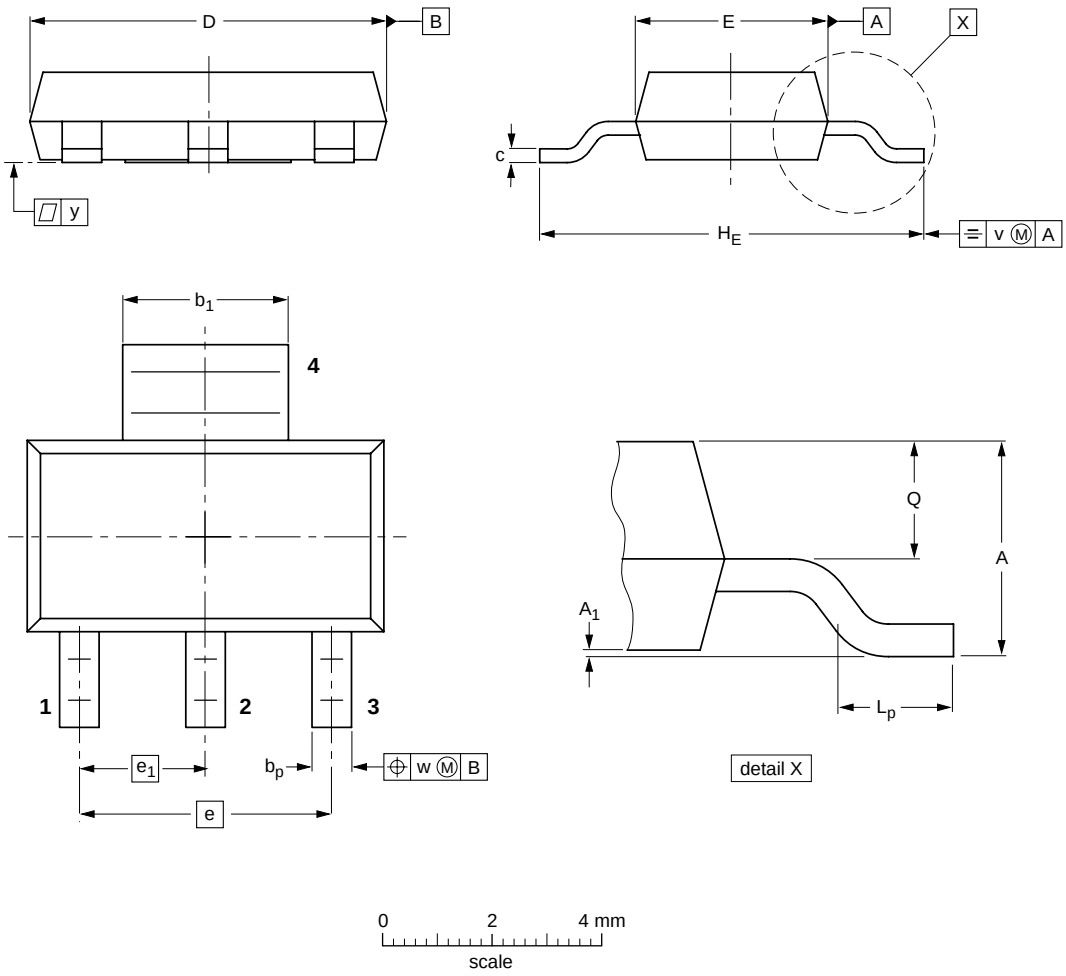


V_i = −9.5 V; T = 500 μs; t_p = 10 μs; t_r = t_f ≤ 3 ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = 3.5 V; V_{CC} = −29.5 V.
Oscilloscope input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			~~97-02-28~~ 99-09-13

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

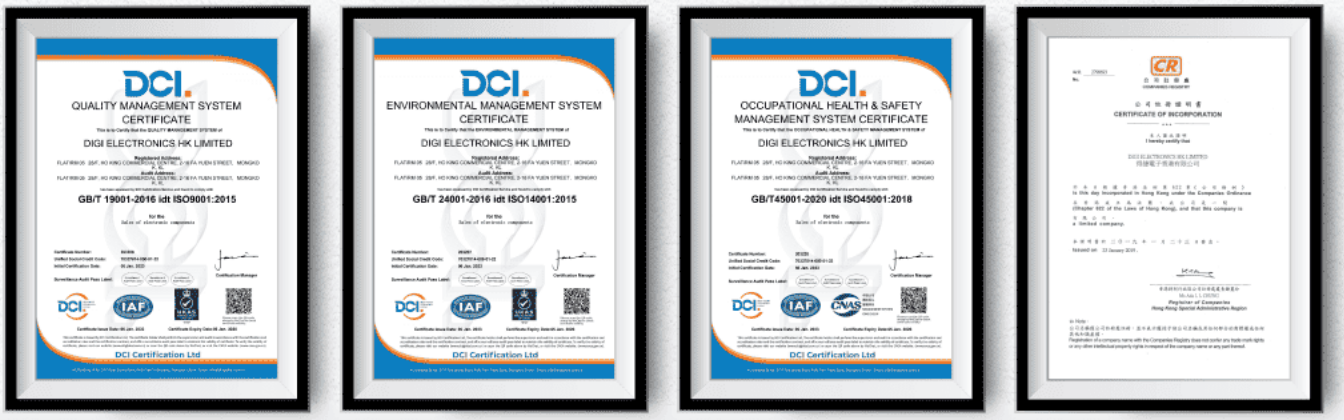
Contact information

For additional information please visit: **http://www.nxp.com**
For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

Printed in The Netherlands 115002/00/03/pp7 Date of release: 1999 Apr 14 Document order number: 9397 750 05637

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.